

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	21372	((opening trench hole via groove damascene) with bottom) with substrate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 09:08
L7	62	6 and (opening trench hole via groove damascene) with ('barc' bottom adj anti adj reflexive)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 09:09
L8	9	7 and (opening trench hole via groove damascene) with (oxide near5 bottom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 09:09
S1	497819	(opening trench hole via groove damascene) with bottom	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 07:31
S2	21372	((opening trench hole via groove damascene) with bottom) with substrate	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 09:08
S3	7046	S2 and (opening trench hole via groove damascene) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 07:33
S4	3451	S3 and (opening trench hole via groove damascene) with (photoresist resist)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 07:33
S5	27	S4 and (opening trench hole via groove damascene) with ('barc' bottom adj anti adj reflexive)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 09:08
S6	8	"6265269"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 07:52
S7	1	"6133099".PN.	USPAT; USOCR	OR	ON	2005/06/24 07:59
S8	1	"6114194".PN.	USPAT; USOCR	OR	ON	2005/06/24 07:59

S9	1	"5937296".PN.	USPAT; USOCR	OR	ON	2005/06/24 07:59
S10	1921	S4 and (opening trench hole via groove damascene) with (oxide with bottom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 08:15
S11	1111	S4 and (opening trench hole via groove damascene) with (oxide near5 bottom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 09:09
S12	944	S4 and (opening trench hole via groove damascene) with (oxide near4 bottom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 08:16
S13	742	S4 and (opening trench hole via groove damascene) with (oxide near3 bottom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 08:16
S14	412	S4 and (opening trench hole via groove damascene) with (oxide near2 bottom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 08:46
S15	125	S4 and (opening trench hole via groove damascene) with (oxide near bottom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/06/24 08:16

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☐ Drafts
☐ Pending
☒ Active
 L6: (21372) ((opening trench ho
 L7: (62) 6 and (opening trench h
 L8: (9) 7 and (opening trench ho
☐ Failed

Search:
 DBs: US-PGPD:USPAT:EPD:JPO
 Default operator: JOR

☒ Purals
☒ Highlight all hit terms initially

7 and (opening trench hole via groove damascene) with (oxide near5 bottom)

	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3
1	<input type="checkbox"/>	US 2005007	2005040	8	Method of manufacturing	438/445			Lin, Chen Tang et a	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 2004026	2004123	16	Single poly-si process for	257/301			Huang, Jenn-Ming	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 2004023	2004112	16	SINGLE POLY-SI PROC	257/296			Huang, Jenn-Ming	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 6875558	2005040	24	Integration scheme using	430/311	427/255.28		Gaillard, Frederic et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 6825078	2004113	16	Single poly-Si process for	438/242	257/296;		Huang, Jenn-Ming	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	US 6733955	2004051	25	Methods for forming self-	430/313	216/17;		Geiger, Fabrice et al	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	US 6607988	2003081	123	Manufacturing method of	438/720	257/E21.3		Yunoganii, Takashi	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
8	<input type="checkbox"/>	US 6544429	2003040	18	Enhancement of silicon o	216/67	216/72;		Hung, Hoiman (Ray	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
9	<input type="checkbox"/>	US 6274426	2001081	12	Self-aligned contact proc	438/253	257/E21.5		Lee, Yu-Hua et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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